

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	42189	semiconductor and cmos	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/04/06 13:44
2	BRS	L2	27258	1 and well	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/04/06 13:44
3	BRS	L3	18364	2 and (substrate or (back adj gate) or backgate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/04/06 13:45
4	BRS	L4	2472	3 and nand	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/04/06 13:47
5	BRS	L5	2231	4 and input and output	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/04/06 13:48

	Comments	Error Definition	Errors
1			0
2			0
3			0
4			0
5			0

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	1348	5 and (threshold adj voltage)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/04/06 13:50
7	BRS	L7	1226	6 and gate and source and drain	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/04/06 13:51

	Comments	Error Definition	Errors
6			0
7			0